**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- Extended temperature range T<sub>i</sub> = 175 °C
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	-80	V	
$V_{GS}$	gate-source voltage	T <sub>j</sub> = 25 °C	[1]	-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[2]	-	-	-1.6	Α	
Static chara	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -1.6 A; $T_j$ = 25 °C		-	170	225	mΩ	

[1] See application node AN90001.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain		G (F)
			1 2	s
			SOT23	017aaa094

# 6. Ordering information

#### Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
PMV170EPA		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23					

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PMV170EPA	XZ%

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-80	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> = 25 °C	[1]	-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[2]	-	-1.6	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[2]	-	-1.1	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-16	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[3]	-	630	mW
			[2]	-	1.3	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode			<u>'</u>		
Is	source current	T <sub>amb</sub> = 25 °C	[2]	-	-1.2	Α
Avalanche r	uggedness	•				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -1 A; DUT in avalanche (unclamped)		-	42	mJ

- [1] See application node AN90001.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [3] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

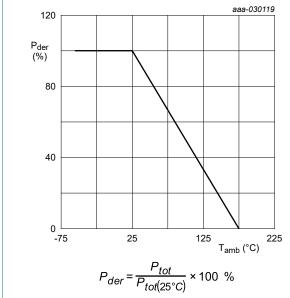


Fig. 1. Normalized total power dissipation as a function of ambient temperature

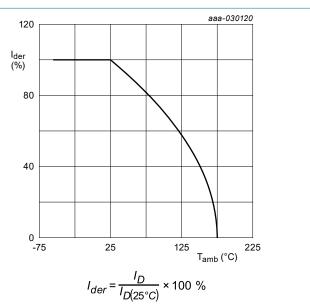


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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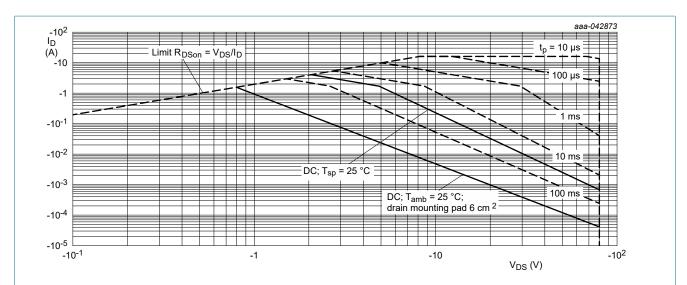


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

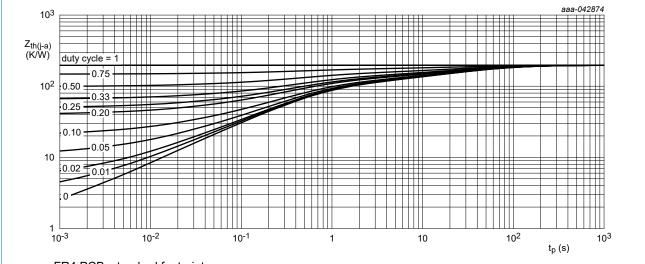
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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	195	240	K/W
junctior	junction to ambient	action to ambient	[2]	-	100	120	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

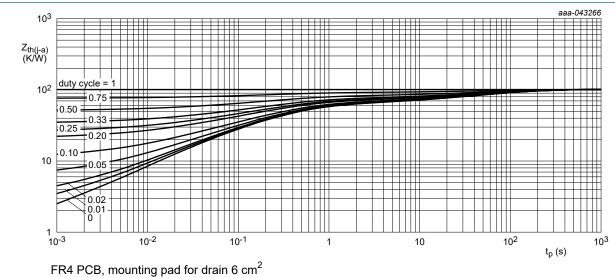


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-80	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-1.4	-2	-2.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nΑ
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -1.6 A; $T_j$ = 25 °C	-	170	225	mΩ
	resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -1.6 A; T <sub>j</sub> = 175 °C	-	380	510	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -1.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	200	270	mΩ
9fs	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -1.6 \text{ A}; T_j = 25 \text{ °C}$	-	4.8	-	S
$R_G$	gate resistance	f = 1 MHz	-	10.5	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -40 V; $I_{D}$ = -1.6 A; $V_{GS}$ = -10 V;	-	10	15	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.7	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	2.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -40 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	535	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	30	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	19	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -40 \text{ V}; I_D = -1.6 \text{ A}; V_{GS} = -10 \text{ V};$	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	22	-	ns
t <sub>f</sub>	fall time	1	-	26	-	ns
Source-drai	in diode		1		1	1
V <sub>SD</sub>	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = -1.2 A; dI <sub>S</sub> /dt = 100 A/μs;	-	19	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = -40 \text{ V}; T_j = 25 \text{ °C}$	_	14	-	nC

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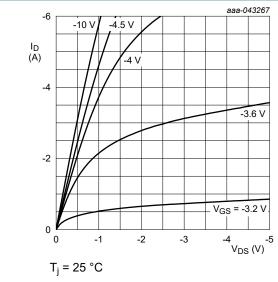


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

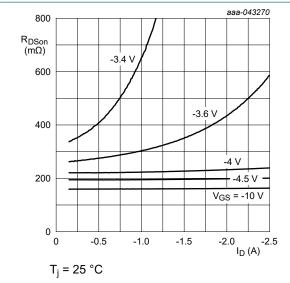


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

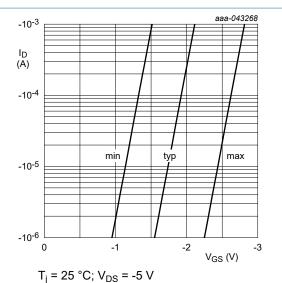


Fig. 7. Subthreshold drain current as a function of

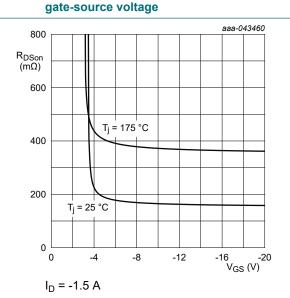


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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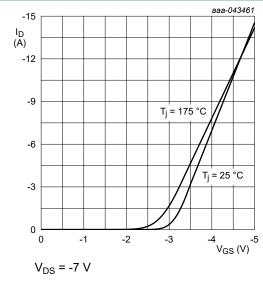


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

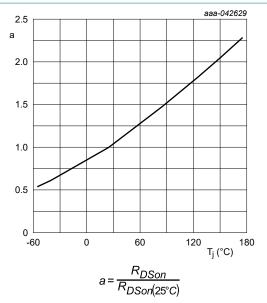


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

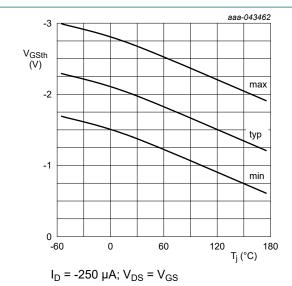


Fig. 12. Gate-source threshold voltage as a function of junction temperature

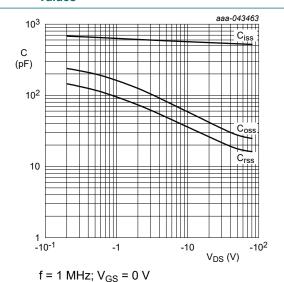


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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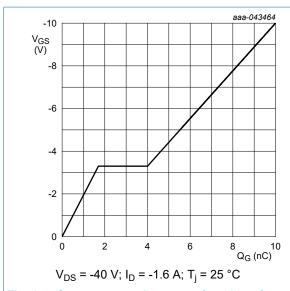


Fig. 14. Gate-source voltage as a function of gate charge; typical values

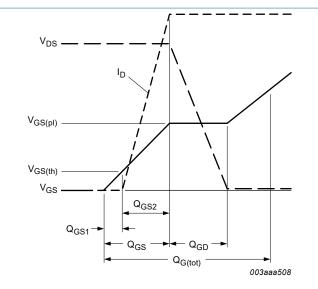


Fig. 15. Gate charge waveform definitions

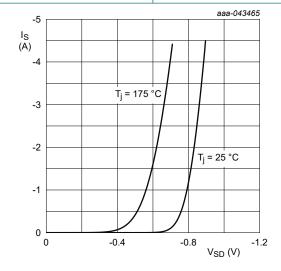


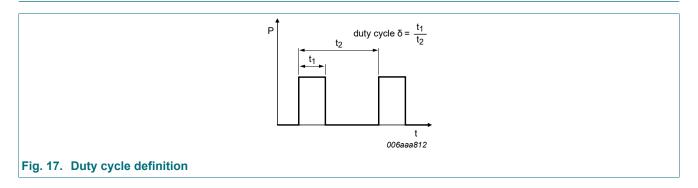
Fig. 16. Source current as a function of source-drain voltage; typical values

1 October 2025

 $V_{GS} = 0 V$ 

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## 11. Test information



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 80 V, P-channel Trench MOSFET

# 12. Package outline

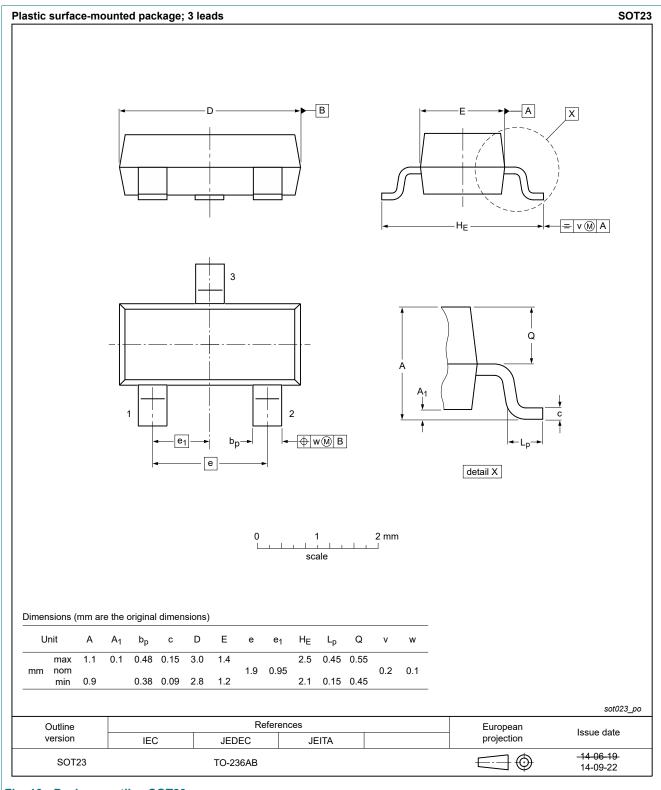
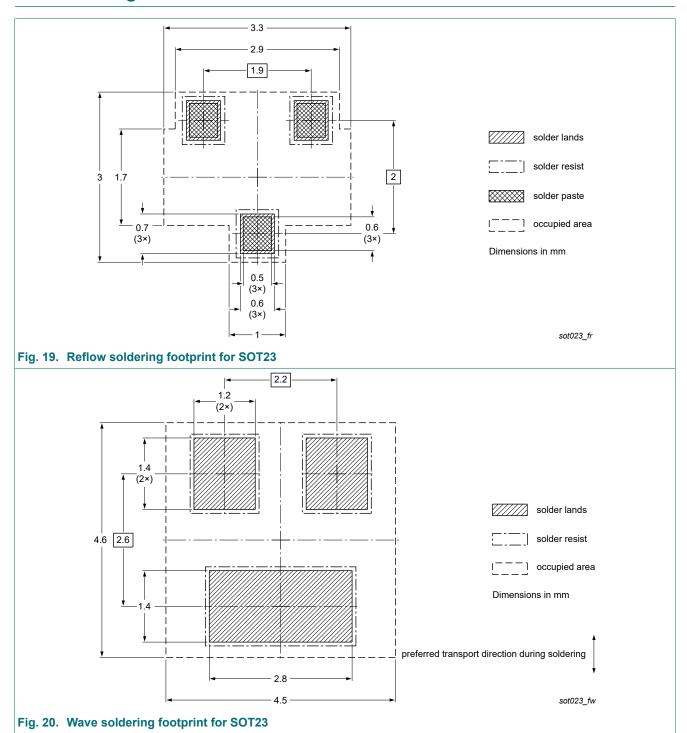


Fig. 18. Package outline SOT23

### 80 V, P-channel Trench MOSFET

# 13. Soldering



80 V, P-channel Trench MOSFET

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV170EPA v.1	20251001	Product data sheet	-	-

### 80 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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